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ELECTRONIC SIGNAL TO NOISE RATIO FOR LA, TMP, AND TMS

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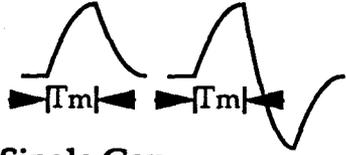
We follow the formulation by Jacques Colas (LBL-27328, Alabama Workshop, 3/89):

$$S/N = \beta I_{max} T_{eff} \sqrt{T_m L / A} = (\beta B q g / 2) \sqrt{T_m L / A}$$

where  $\beta=4.3$  for LA and 3.8 for TMP or TMS,  $I_{max}$  is the initial current in ke/ $\mu$ sec in the triangular pulse of length  $T_d$ =drift time.  $T_m$  is the measurement time; we use the shaper response shown in the left figure below.  $L(m)$  and  $A(sq\ m)$  are the sum in depth of gap widths, and the area of each gap, respectively.  $T_{eff}$  is the effective time during which the shaper collects charge. Using the drift velocity  $v_d(cm/\mu sec)=g/T_d=I_{max}/q$ ,  $N$  may be expressed also in terms of the gap width  $g(cm)$ , the linear charge density  $q(ke/cm)$ , and a 'ballistic' factor:

$$B = 2T_{eff}/T_d \approx (1.27T_m/T_d)[1-\exp(-T_d/1.27T_m)] \leq 1,$$

which measures the effective fractional charge utilization. A small value for  $B$  implies a greater relative sensitivity to pile-up. Greater rejection of pile-up could be achieved, with a factor  $\sqrt{3}$  increase in noise, using the fast bipolar shaping function shown at the right below.



**Single Gap**

At the right we show  $S/N$  and  $B$  for mipis in one gap: i.e., we take:

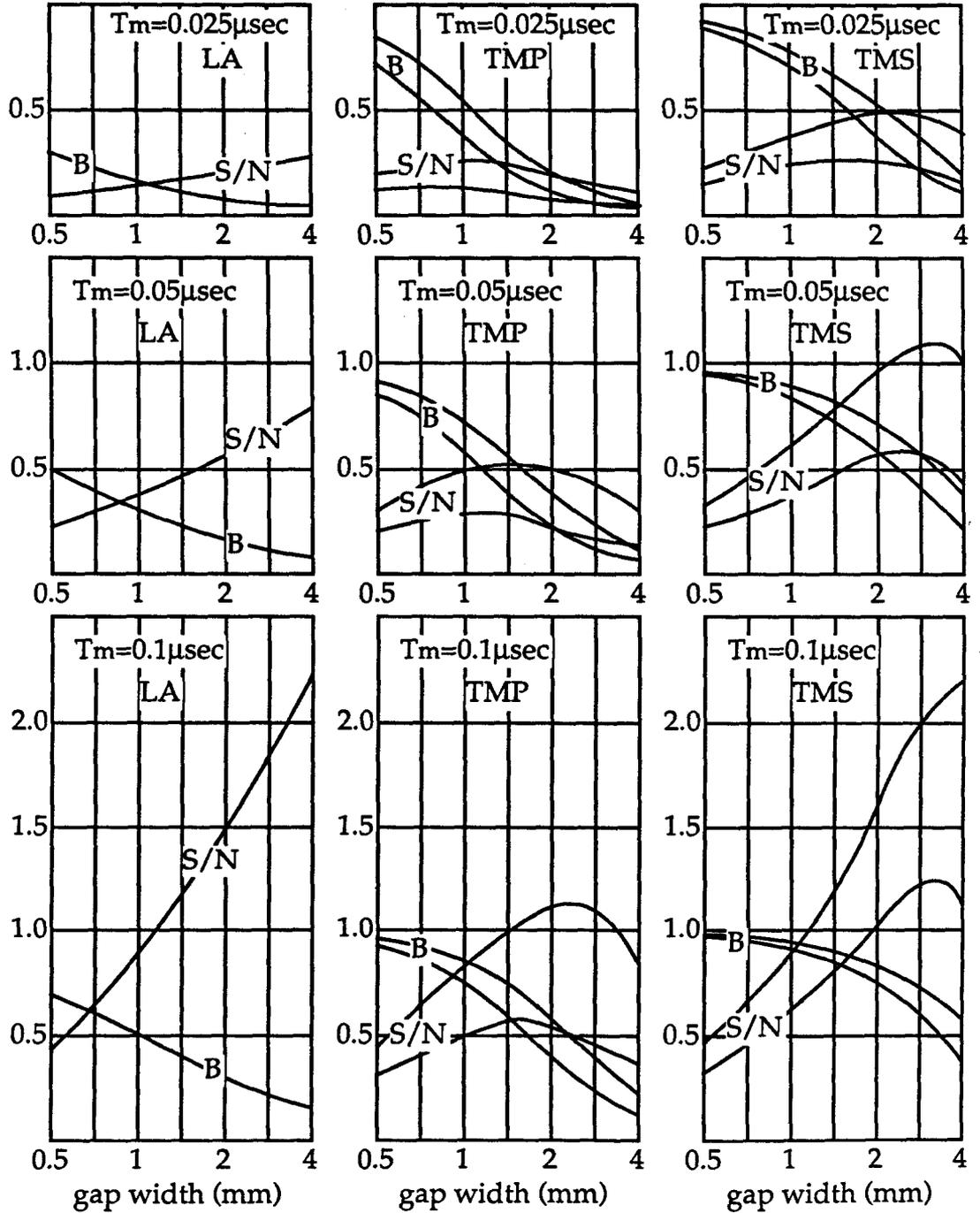
- $L(m)=0.01g(cm)$
- $A=0.01\ sq\ m.$

**For LA**

- $E=V/g$  is taken to be 10kV/cm; the performance is not sensitive to this value.
- $S/N \propto T_m \sqrt{gT_m}$
- $B$  is generally small for large  $g$ .

**For TMP and TMS**

- Both  $T_d$  and  $q$  are functions of  $E$ . We use  $V = 5$  or  $10$  kV. The maximum voltage is assumed to be set by the feedthroughs and insulators rather than the liquid gap width.
- For both  $S/N$  and  $B$  the 10kV curves lie above those for 5kV.
- Trade-off of  $I_{max}$  and capacitance produces a peak in  $S/N$  vs  $g$  with:
  - $(S/N)_{max} \propto \sqrt{VT_m}$
  - $g_{max} \propto \sqrt{VT_m}$ .
  - $B(g_{max}) \approx 0.5$ .
- $S/N_{TMS} / S/N_{TMP} \approx 2$



In the calculations above we have ignored the implications of the  $g$ -dependence of calorimeter density, absorber thickness, relative gap tolerances, etc, each of which affects the resolution. As an example, the total depth of liquid may be limited to achieve  $e/h$  compensation or to maintain a large average calorimeter density. Then larger gap width implies poorer sampling and resolution.

**Fixed Liquid Depth**

If the total liquid depth ( $L=\Sigma g$ ) is specified, there is a trade-off between gap width and gap number. e.g.,  $L=0.1m$  represents 50 gaps of 2mm width or 100 gaps of 1mm width, etc. Here we consider specifically  $S/N$  for a liter of liquid, i.e., with:

$L=0.1 m, A=0.01 \text{ sq m.}$

Then each  $S/N$  is obtained from that calculated previously by multiplying by  $\sqrt{10/g(\text{cm})}$ .  $B(g)$  is unchanged. Below are calculated values of  $S/N$  and  $B$  for the same liquids and values of  $T_m$  used in the single gap example above.

- Compared with the single gap solution,  $S/N$  is now maximized at smaller gaps, where  $B$  is larger.
- For most cases,  $S/N > 1$ ; hence mips are detectable in this tower section.

For LA

- $B$  values are small, but  $S/N$  is only moderately, if at all, dependent on  $g$ ; a small gap minimizes pile-up.

For TMP, TMS

- $S/N$  peaks are shifted to smaller gaps.
- $(S/N)_{\text{max}} \propto T_m$ ; the dependence on  $V$  is slightly less than linear.
- $g_{\text{max}} \propto \sqrt{T_m}$ ; the dependence on  $V$  is slightly less than  $\sqrt{\text{g}}$ .
- $B(g_{\text{max}}) \approx 0.7-0.8$  - pile-up is small -
- At each  $V$  and  $T_m$ , the peak value of  $S/N$  for TMS is  $\sqrt{2}$  times larger than for TMP.
- At  $T_m=0.05\mu\text{sec}$ , the  $S/N$  peaks are at:  
 $g \approx 1 \text{ mm}$  for TMP  
 $g \approx 2 \text{ mm}$  for TMS

